

NXH003P120M3F2PTNG

Silicon Carbide (SiC) Module – EliteSiC, 3 mohm SiC M3S MOSFET, 1200 V, 2-PACK Half Bridge Topology, F2 Package

Product Overview

For complete documentation, see the data sheet.

The NXH003P120M3F2PTNG is a power module containing 3 mohm / 1200 V SiC MOSFET halfbridge and a thermistor with Si3N4 DBC in an F2 package. The SiC MOSFET switches use M3S technology and are driven with 18V-20V gate drive.

Features


- 15V to 18V Gate Drive
- 3 mohm / 1200V M3S SiC MOSFET Half-Bridge
- Pb-Free, Halide Free and are RoHS Compliant

Applications

- DC-AC Conversion
- DC-DC Conversion
- AC-DC Conversion

End Products

- UPS
- Energy Storage Systems
- Electric Vehicle Charging Stations
- Solar Inverters

Part Electrical Specifications												
Product	Status	Compliance	Configuration	V _{BR} Max (V)	R _{DS(on)} Typ (mΩ)	Application	Package Type	Case Outline	MSL Type	MSL Temp (°C)	Container Type	Container Qty.
NXH003P120M3F2PTNG	Active		Half-Bridge	1200	3	EV Charging, Energy Infrastructure	PIM36 56.7x4 2.5 (PRESS FIT)	180BY. PDF	NA	0	BTRAY	20